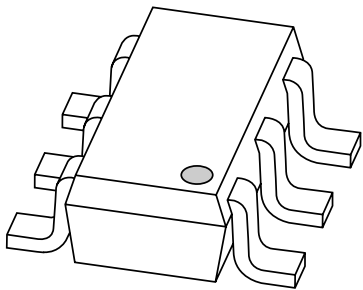


# DATA SHEET



## **PMBT3904D** NPN switching double transistor

Product specification

1999 Dec 15

# NPN switching double transistor

# PMBT3904D

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and board space.

### APPLICATIONS

- Telephony and professional communication equipment.

### DESCRIPTION

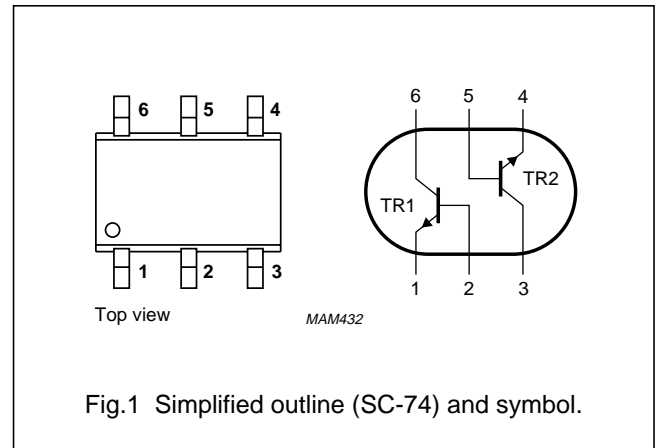
Two independently operating NPN switching transistors in a SC-74, six lead, SMD plastic package.

### MARKING

TYPE NUMBER	MARKING CODE
PMBT3904D	D1

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
V <sub>CB0</sub>	collector-base voltage	open emitter	–	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	6	V
I <sub>C</sub>	collector current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	300	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	600	mW

### Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

## NPN switching double transistor

## PMBT3904D

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	208	K/W

## Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

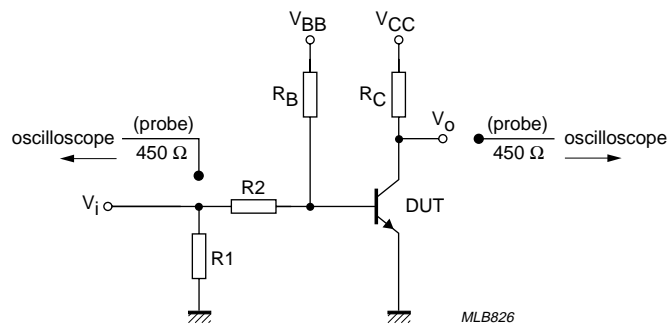
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 6\text{ V}$	–	50	nA
$h_{FE}$	DC current gain	$V_{CE} = 1\text{ V}$ ; note 1; Fig.3 $I_C = 0.1\text{ mA}$ $I_C = 1\text{ mA}$ $I_C = 10\text{ mA}$ $I_C = 50\text{ mA}$ $I_C = 100\text{ mA}$	60 80 100 60 30	– – 300 – –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	200	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	200	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	650	850	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	950	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	4	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{BE} = 500\text{ mV}; f = 1\text{ MHz}$	–	8	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	300	–	MHz
F	noise figure	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$	–	5	dB
<b>Switching times (between 10% and 90% levels); (see Fig.2)</b>					
$t_{on}$	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 1\text{ mA}; V_{CC} = 3\text{ V};$ $V_{BB} = -1.9\text{ V}$	–	65	ns
$t_d$	delay time		–	35	ns
$t_r$	rise time		–	35	ns
$t_{off}$	turn-off time		–	240	ns
$t_s$	storage time		–	200	ns
$t_f$	fall time		–	50	ns

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

## NPN switching double transistor

## PMBT3904D

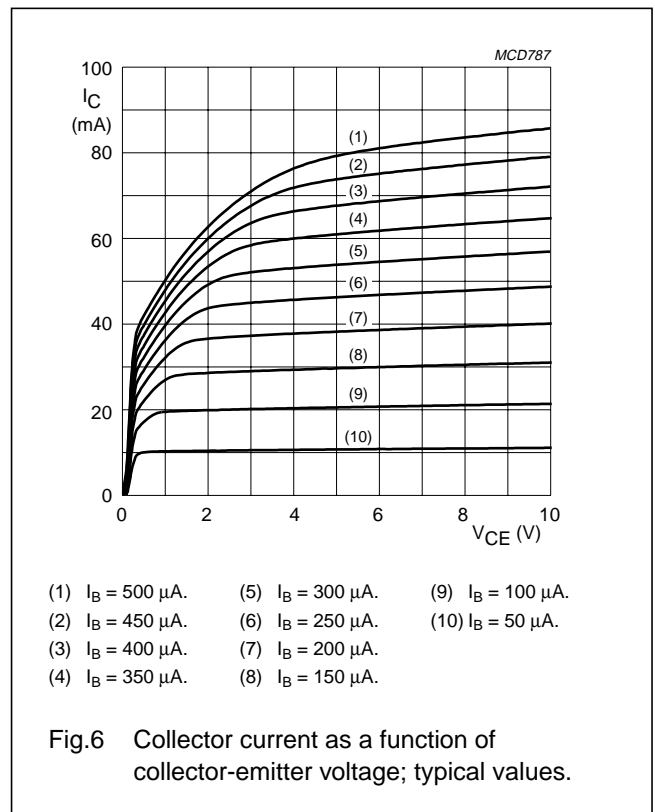
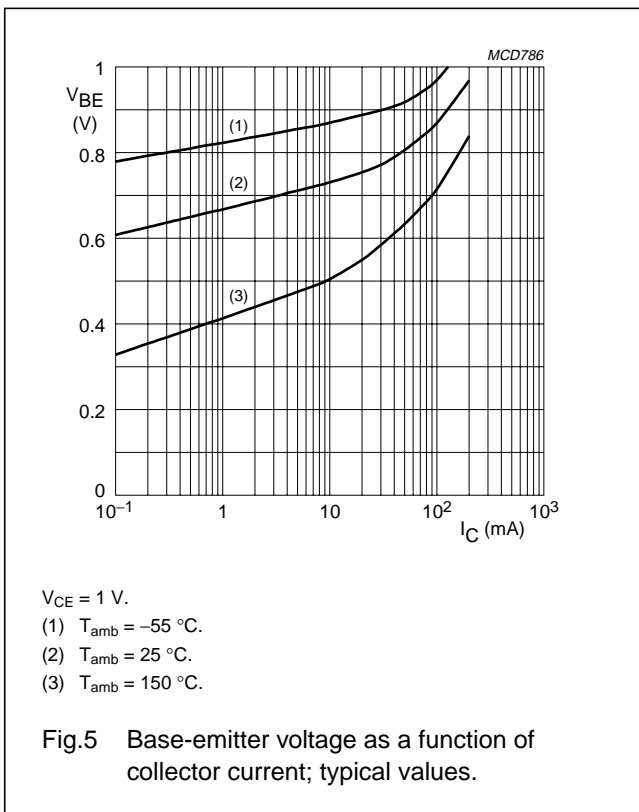
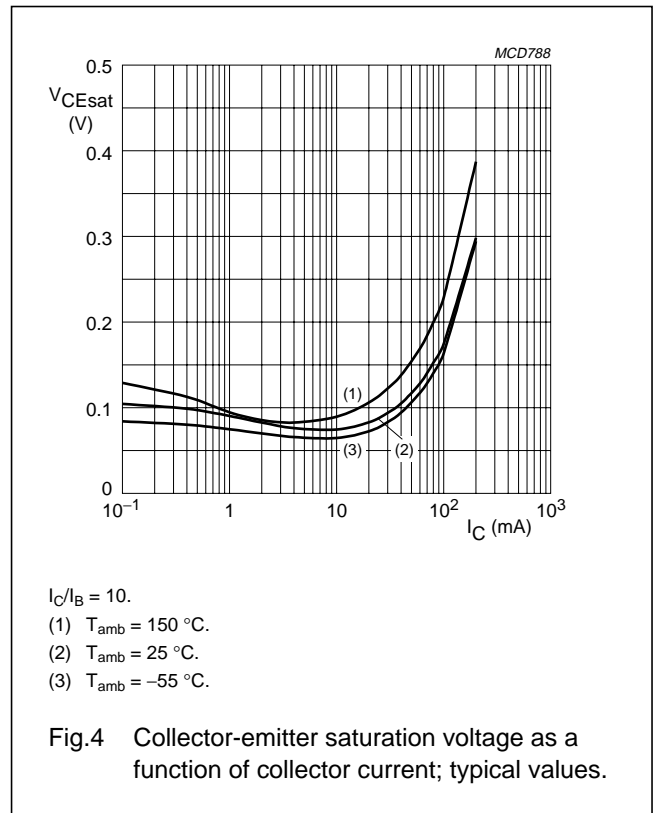
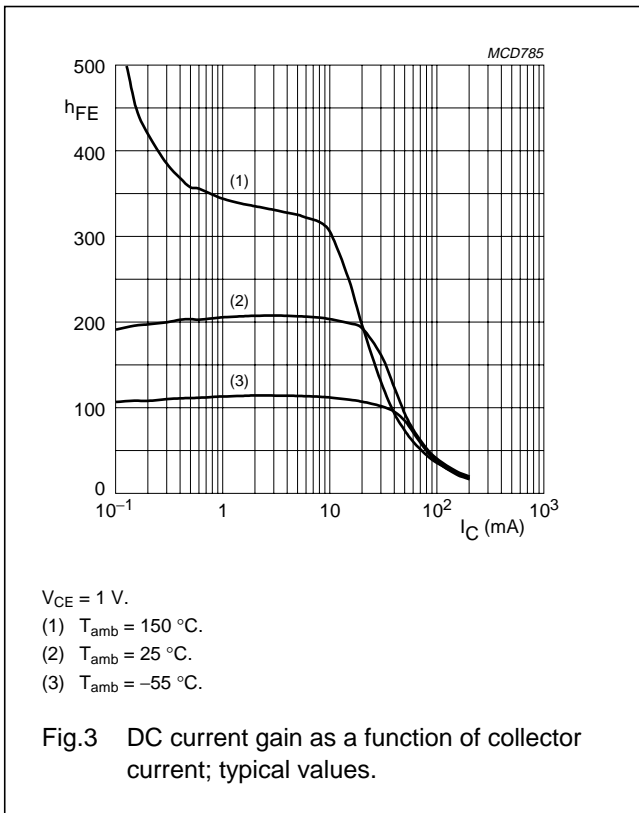


$V_i = 5 \text{ V}$ ;  $T = 600 \mu\text{s}$ ;  $t_p = 10 \mu\text{s}$ ;  $t_r = t_f \leq 3 \text{ ns}$ .  
 $R_1 = 56 \Omega$ ;  $R_2 = 2.5 \text{ k}\Omega$ ;  $R_B = 3.9 \text{ k}\Omega$ ;  $R_C = 270 \Omega$ .  
 $V_{BB} = -1.9 \text{ V}$ ;  $V_{CC} = 3 \text{ V}$ .  
Oscilloscope: input impedance  $Z_i = 50 \Omega$ .

Fig.2 Test circuit for switching times.

NPN switching double transistor

PMBT3904D



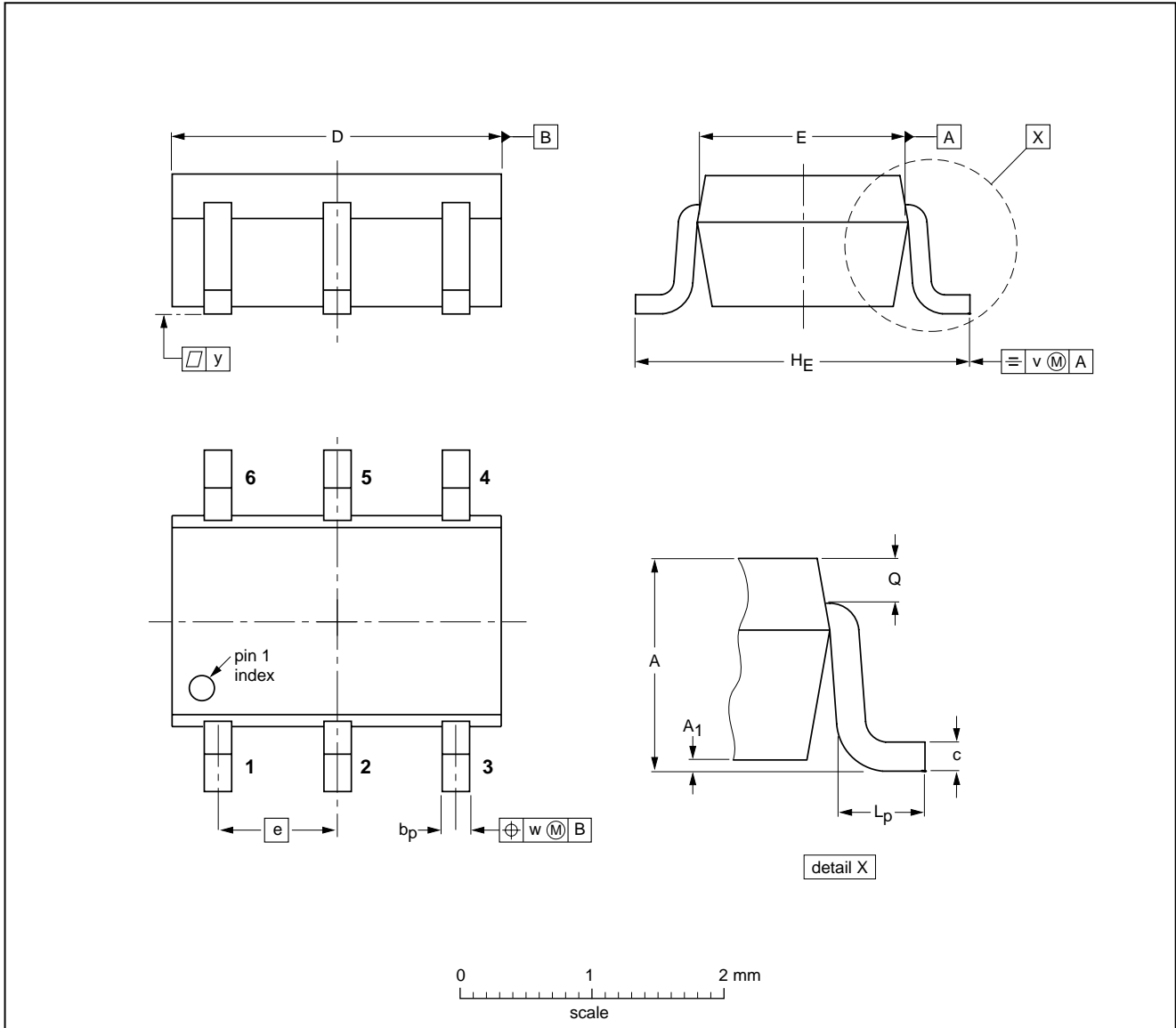
NPN switching double transistor

PMBT3904D

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	bp	c	D	E	e	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT457			SC-74			97-02-28

## NPN switching double transistor

PMBT3904D

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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